

and comprising means for preventing pollution of the circuit elements and of the substrate by hydrogen originating from an environment inside a housing enclosing a portion of the semiconductor device, characterized in that said means are formed by a layer of a material which absorbs hydrogen, referred to as hydrogen getter (10), which forms a pattern which is [integrated with the circuit elements] and of which an external surface (11) is exposed and in contact with said environment.

cont
B3 2. (Amended) A device as claimed in claim 1, characterized in that the hydrogen getter layer is formed on a surface of the substrate and in that the circuit elements comprise an upper protective layer which has an opening for exposing the upper surface (11) of said hydrogen getter layer (10).

B4 4. (Amended) A device as claimed in claim 1, characterized in that the hydrogen getter layer forms patterns arranged between the integrated circuit elements or patterns arranged along a periphery of the integrated circuits.

REMARKS

This application has been carefully reviewed in light of the Office Action dated March 30, 2001. Claims 1-7 and 9-10 are